

In the Claims:

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(C)

Claim 2 (amended). The process according to claim 1, wherein a further amorphous layer that extends to a predetermined depth into the semiconductor substrate is produced by ion bombardment before a heat treatment step.

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Claim 4 (amended). The process according to claim 2, which comprises forming the further amorphous layer to have a thickness of between 500 - 1000 nm.

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Claim 11 (amended). The process according to claim 10, which comprises carrying out the ion implantation process using ions selected from the group consisting of B, P, As, In and Sb ions.